

Optocoupler with Phototransistor Output

Order Nos. and Classification table is on sheet 2.

Description

The CNY17 series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6-lead plastic dual inline package.

coplanar technique, providing a fixed distance between input and output for highest safety requirements.

The elements are mounted on one leadframe using a





Applications

Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):

- For application class I IV at mains voltage ≤ 300 V
- For application class I III at mains voltage ≤ 600 V according to VDE 0884, table 2, suitable for:

Switch-mode power supplies, computer peripheral interface, microprocessor system interface, line receiver.

These couplers perform safety functions according to the following equipment standards:

• VDE 0884

Optocoupler providing protective separation

- VDE 0804 Telecommunication apparatus and data processing
- VDE 0805/IEC 950/EN 60950 Office machines (applied for reinforced isolation for mains voltages ≤ 400 V_{RMS})
- VDE 0860/IEC 65

Safety for mains operated electronic and related household apparatus



Features

According to VDE 0884

- Rated impulse voltage (transient overvoltage) V_{IOTM} = 6 kV peak
- Isolation test voltage (partial discharge test voltage) V_{pd} = 1.6 kV
- Rated isolation voltage (RMS includes DC) V_{IOWM} = 600 V_{RMS} (848 V peak)
- Rated recurring peak voltage (repetitive) V_{IORM} = 600 V_{RMS}
- Creeping current resistance according to VDE 0303/IEC 112 Comparative Tracking Index: CTI = 275
- Thickness through insulation ≥ 0.75 mm

- Further approvals: BS 415, BS 7002, SETI: IEC 950, UL 1577: File No: E 76222
- CTR offered in 3 groups
- Isolation materials according to UL 94-VO
- Pollution degree 2 (DIN/VDE 0110 part 1 resp. IEC 664)
- Climatic classification 55/100/21 (IEC 68 part 1)
- Special construction: Therefore extra low coupling capacity of typical 0.3 pF, high Common Mode Rejection
- Low temperature coefficient of CTR

Order Schematic

Part Numbers	CTR-Ranking
CNY17-1/ CNY17G-1/ CNY17S-1/ CNY17GS-1	40 - 80%
CNY17-2/ CNY17G-2/ CNY17S-2/ CNY17GS-2	63 - 125%
CNY17-3/ CNY17G-3/ CNY17S-3/ CNY17GS-3	100 - 200%

Suffix: G = Leadform 10.16 mm

S = Waterproofed device

Remarks

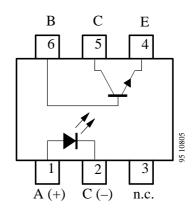
A waterproof construction is recommended for couplers where a pure water cleaning process is used instead of a standard-soldering/cleaning process. In this case please order the part numbers with the suffix "S".

The waterproof construction corresponds with the coupling system "S", and does not belong to the part number itself.

Standard parts are marked with the letter "A".

This coupling system indicator "A" or "S" is in a separate (second) line of the marking.

Pin Connection





Absolute Maximum Ratings

Input (Emitter)

Parameters	Test Conditions	Symbol	Value	Unit
Reverse voltage		VR	5	V
Forward current		IF	60	mA
Forward surge current	$t_p \le 10 \ \mu s$	I _{FSM}	3	А
Power dissipation	$T_{amb} \le 25^{\circ}C$	P _{tot}	100	mW
Junction temperature		Ti	125	°C

Output (Detector)

Parameters	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V _{CEO}	32	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		IC	50	mA
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	100	mA
Power dissipation	$T_{amb} \le 25^{\circ}C$	P _{tot}	150	mW
Junction temperature		Tj	125	°C

Coupler

Parameters	Test Conditions Symbol Valu		Value	Unit
Isolation test voltage (RMS)		V _{IO}	3.75	kV
Total power dissipation	$T_{amb} \le 25^{\circ}C$	P _{tot}	250	mW
Ambient temperature range		T _{amb}	-55 to +100	°C
Storage temperature range		T _{stg}	-55 to +125	°C
Soldering temperature	2 mm from case, t \leq 10 s	T _{sd}	260	°C

Maximum Safety Ratings¹ (according to VDE 0884)

Input (Emitter)

Parameters	Test Conditions	Symbol	Value	Unit
Forward current		I _{si}	130	mA

Output (Detector)

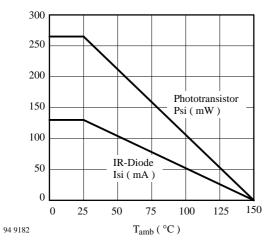
Parameters	Test Conditions	Symbol	Value	Unit
Power dissipation	$T_{amb} \le 25^{\circ}C$	P _{si}	265	mW

Coupler

Parameters	Test Conditions	Symbol	Value	Unit
Rated impulse voltage		V _{IOTM}	6	kV
Safety temperature		T _{si}	150	°C

¹⁾ This device is used for protective separation against electrical shock only within the maximum ratings. This must be ensured by using protective circuits in the applications.

Derating Diagram



Electrical Characteristics

$T_{amb} = 25^{\circ}C$

Input (Emitter)

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	$I_F = 50 \text{ mA}$	V _F		1.25	1.6	V
Breakdown voltage	$I_{C} = 100 \ \mu A$	V _(BR)	5			V
Junction capacitance	$V_{R} = 0, f = 1 MHz$	Ci		50		pF

Output (Detector)

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector emitter breakdown voltage	$I_C = 1 mA$	V _{(BR)CEO}	32			V
Emitter collector breakdown voltage	$I_E = 100 \ \mu A$	V _{(BR)ECO}	7			V
Collector emitter cut-off current	$V_{CE} = 10 \text{ V}, I_f = 0$	I _{CEO}		10	100	nA

Coupler

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
AC isolation test voltage (RMS)	f = 50 Hz, t = 1 s	V _{IO}	3.75			V
Collector/emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V _{CEsat}			0.3	V
Cut-off frequency	$\label{eq:Vce} \begin{split} V_{CE} &= 5 \ V, \ I_F = 10 \ mA, \\ R_L &= 100 \ \Omega \end{split}$	f_c		110		kHz
Coupling capacitance	f = 1 MHz	Ck		0.3		pF

Current Transfer Ratio (CTR)

Parame- ters	Test Conditions	Туре	Symbol	Min.	Тур.	Max.	Unit
I _C /I _F	$V_{CE} = 5 V, I_F = 10 mA$	CNY17-1	CTR	0.4		0.8	
I _C /I _F	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}$	CNY17-2	CTR	0.63		1.25	
I_C/I_F	$V_{CE} = 5$ V, $I_F = 10$ mA	CNY17-3	CTR	1.0		2.0	
I_C/I_F	$V_{CE} = 5 \text{ V}, I_F = 1 \text{ mA}$	CNY17-1	CTR	0.13			
I _C /I _F	$V_{CE} = 5 \text{ V}, I_F = 1 \text{ mA}$	CNY17-2	CTR	0.22			
I_C/I_F	$V_{CE} = 5 V, I_F = 1 mA$	CNY17-3	CTR	0.34			

Switching Characteristics (Typical Values)

 $V_S = 5 V$

Trino		$R_L = 100 \Omega$ (see figure 2)						$R_L = 1 k\Omega$ (see figure 3)		
Туре	t _d [µs]	t _r [µs]	t _{on} [µs]	t _s [µs]	t _f [µs]	t _{off} [µs]	I _C [mA]	t _{on} [µs]	t _{off} [µs]	I _F [mA]
CNY17-1 to 3	4.0	7.0	11.0	0.3	6.7	7.0	5.0	25.0	42.5	10.0

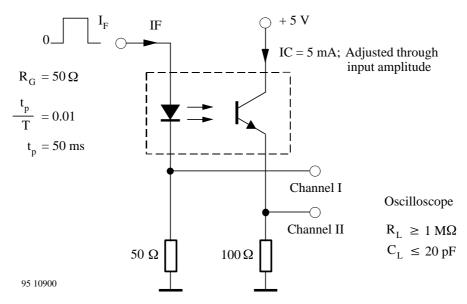


Figure 1. Test circuit, non-saturated operation

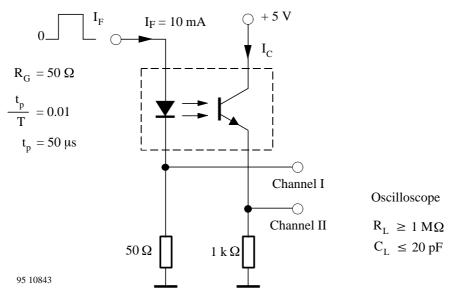
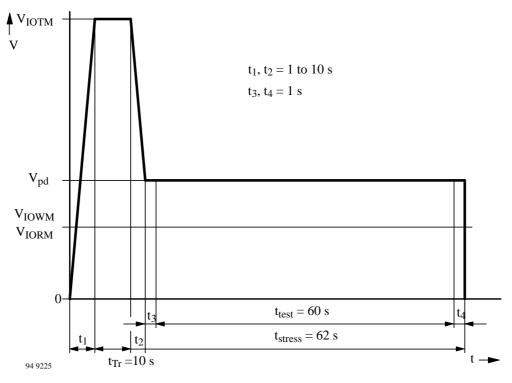


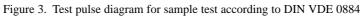
Figure 2. Test circuit, saturated operation



Insulation Rated Parame	ters (accordin	ng to VD	E 0884)	
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Parameters		Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Partial discharge test voltage Routine test Lot test (sample test)	100%, $t_{test} = 1 s$	V _{pd}	1.6			kV	
	$t_{\rm Tr} = 10 \rm s,$	V _{IOTM}	6			kV	
	(sample test)	$t_{test} = 60 s$ (see figure 3)	V _{pd}	1.3			kV
Insulation resistance		$V_{IO} = 500 \text{ V}$	R _{IO}	1012			Ω
		$V_{IO} = 500 \text{ V},$ $T_{amb} = 100^{\circ}\text{C}$	R _{IO}	10 ¹¹			Ω
monation resistance	$V_{IO} = 500 \text{ V},$ $T_{amb} = 150^{\circ}\text{C}$	R _{IO}	10 ⁹			Ω	
		(construction test only)					





Typical Characteristics ($T_{amb} = 25^{\circ}C$, unless otherwise specified)

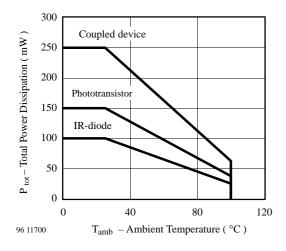


Figure 4. Total Power Dissipation vs. Ambient Temperature

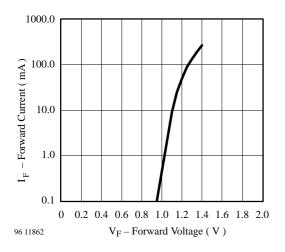


Figure 5. Forward Current vs. Forward Voltage

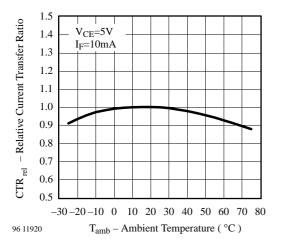


Figure 6. Rel. Current Transfer Ratio vs. Ambient Temperature

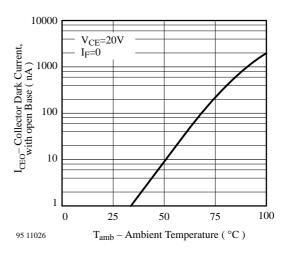


Figure 7. Collector Dark Current vs. Ambient Temperature

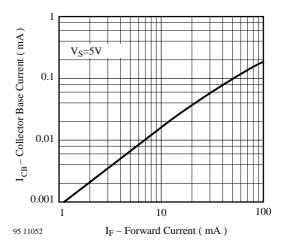


Figure 8. Collector Base Current vs. Forward Current

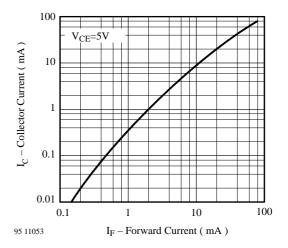


Figure 9. Collector Current vs. Forward Current

Typical Characteristics ($T_{amb} = 25^{\circ}C$, unless otherwise specified)

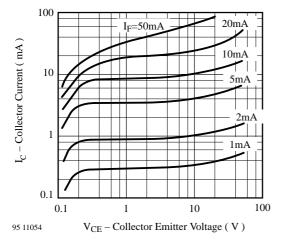


Figure 10. Collector Current vs. Collector Emitter Voltage

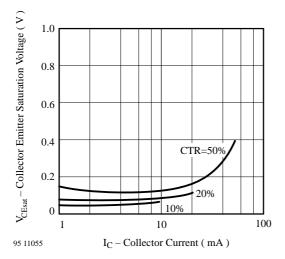


Figure 11. Collector Emitter Sat. Voltage vs. Collector Current

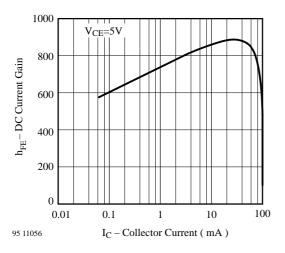


Figure 12. DC Current Gain vs. Collector Current

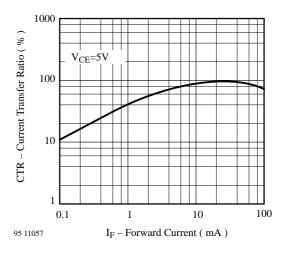


Figure 13. Current Transfer Ratio vs. Forward Current

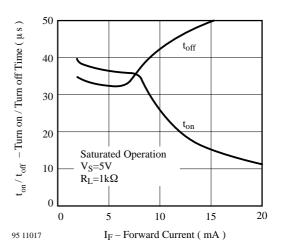


Figure 14. Turn on / off Time vs. Forward Current

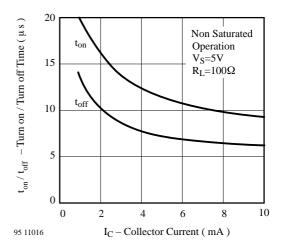
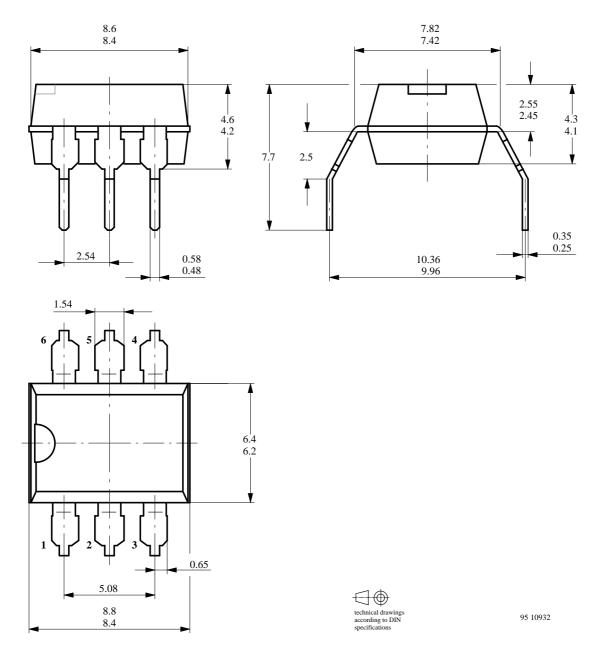


Figure 15. Turn on / off Time vs. Collector Current

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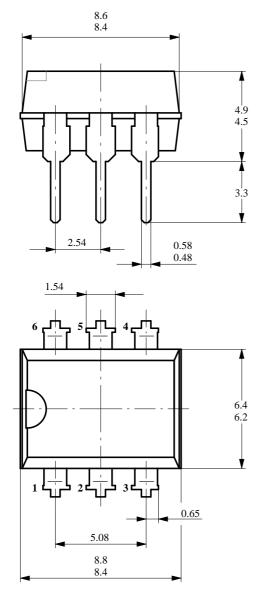
Dimensions in mm

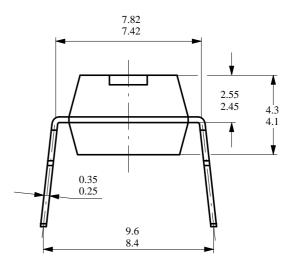
Leadform 10.16. mm (G-type)





Dimensions in mm







95 10931

Ozone Depleting Substances Policy Statement

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

TEMIC TELEFUNKEN microelectronic GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423